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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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COMPLEMENTARY NPN/PNP PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

Features

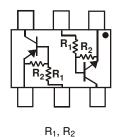
- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

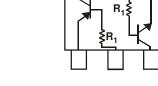
P/N	R1 (NOM)	R2 (NOM)	MARKING
DCX122LH	0.22ΚΩ	10ΚΩ	C81
DCX142JH	0.47 K Ω	10ΚΩ	C82
DCX122TH	0.22 K Ω	OPEN	C83
DCX142TH	0.47ΚΩ	OPEN	C84

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208@3
- Terminal Connections: See Diagram
- Weight: 0.005 grams (Approximate)

SOT-563





R₁ Only

SCHEMATIC DIAGRAM, TOP VIEW

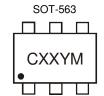
Ordering Information (Note 4)

Device	Packaging	Shipping
DCX122LH-7	SOT-563	3,000/Tape & Reel
DCX142JH-7	SOT-563	3,000/Tape & Reel
DCX122TH-7	SOT-563	3,000/Tape & Reel
DCX142TH-7	SOT-563	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



CXX = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Ī	Date Code Ney	2222	2222	2024	2225	2222	2007	2008	2009	2010	2011	2012
	Year	2002	2003	2004	2005	2006	2007	2006	2009	2010	2011	2012
	Code	N	Р	R	S	Т	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings NPN Section (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		V _{CC}	50	V
Input Voltage	DCX122LH DCX142JH	V _{IN}	-5 to +6 -5 to +6	V
Input Voltage	DCX122TH DCX142TH	V _{EBO (MAX)}	5	V
Output Current	All	I _C	100	mA
Power Dissipation	(Notes 5 & 6)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Maximum Ratings PNP Section (@TA = +25°C unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Supply Voltage		Vcc	-50	V
Input Voltage	DCX122LH DCX142JH	V _{IN}	+5 to -6 +5 to -6	V
Input Voltage	DCX122TH DCX142TH	V _{EBO} (MAX)	-5	V
Output Current	All	Ic	-100	mA
Power Dissipation	(Notes 5 & 6)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air	(Note 5)	$R_{ hetaJA}$	833	°C/W
Operating and Storage Temperature Range		T _j , T _{STG}	-55 to +150	°C

Notes:

- 5. Mounted on FR4 PC Board with recommended pad layout at http://www.diodes.com/datasheets/ap02001.pdf.
- 6. NPN Section, PNP Section, or maximum combined.



Electrical Characteristics NPN Section, R1, R2 Types (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH	$V_{I(off)}$	0.3 0.3			٧	$V_{CC} = 5V, I_{O} = 100\mu A$
	DCX122LH DCX142JH	V _{I(on)}			2.0 2.0	٧	$V_O = 0.3V$, $I_O = 20mA$ $V_O = 0.3V$, $I_O = 20mA$
Output Voltage		$V_{O(on)}$			0.3V	٧	$I_{O}/I_{I} = 5\text{mA}/0.25\text{mA}$
Input Current	DCX122LH DCX142JH	l _l	_	_	28 13	mA	V _I = 5V
Output Current		I _{O(off)}		_	0.5	μА	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	DDCX122LH DDCX142JH	Gı	56 56			_	V _O = 5V, I _O = 10mA
Gain-Bandwidth Product*		f _T		200	١	MHz	$V_{CE} = 10V, I_E = 5mA, f = 100MHz$

^{*} Transistor - For Reference Only

Electrical Characteristics NPN Section, R1-Only (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	50	_	_	٧	$I_C = 50\mu A$
Collector-Emitter Breakdown Voltage		BV _{CEO}	40	_	_	V	I _C = 1mA
Emitter-Base Breakdown Voltage	DCX122TH DCX142TH	BV _{EBO}	5			V	I _E = 50μA I _E = 50μA
Collector Cut-Off Current		I _{CBO}	_	_	0.5	μΑ	V _{CB} = 50V
Emitter Cut-Off Current	DCX122TH DCX142TH	I _{EBO}			0.5 0.5	μΑ	V _{EB} = 4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}			0.3	٧	I _C = 5mA, I _B = 0.25mA
DC Current Transfer Ratio	DCX122TH DCX142TH	h _{FE}	100 100	250 250	600 600		I _C = 1mA, V _{CE} = 5V
Gain-Bandwidth Product*		f⊤	_	200	_	MHz	$V_{CE} = 10V$, $I_E = -5mA$, $f = 100MHz$

^{*} Transistor - For Reference Only

Electrical Characteristics PNP Section, R1, R2 Types (@T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH	$V_{I(off)}$	-0.3 -0.3	_		٧	$V_{CC} = -5V$, $I_O = -100\mu A$
	DCX122LH DCX142JH	$V_{I(on)}$		_	-2.0 -2.0		$V_O = -0.3V$, $I_O = -20mA$ $V_O = -0.3V$, $I_O = -20mA$
Output Voltage		$V_{O(on)}$		_	-0.3V	٧	$I_{O}/I_{I} = -5mA/-0.25mA$
Input Current	DCX122LH DCX142JH	I _I	_	_	-28 -13	mA	V _I = -5V
Output Current		I _{O(off)}		_	-0.5	μΑ	$V_{CC} = -50V, V_1 = 0V$
DC Current Gain	DCX122LH DCX142JH	G _l	56 56	_			$V_O = -5V, I_O = -10mA$
Gain-Bandwidth Product*		f⊤		200		MHz	V _{CE} = -10V, I _E = -5mA, f = 100MHz

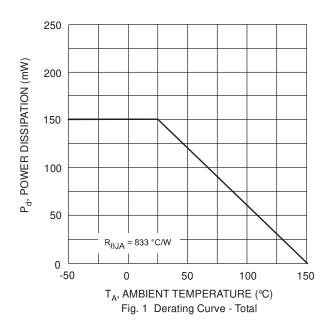
^{*} Transistor - For Reference Only



Electrical Characteristics, R1-Only Types @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-50	_	_	V	$I_C = -50\mu A$
Collector-Emitter Breakdown Voltage	,	BV _{CEO}	-40	_	_	V	I _C = -1mA
Emitter-Base Breakdown Voltage	DCX122TH DCX142TH	BV _{EBO}	-5			>	I _E = -50μA I _E = -50μA
Collector Cut-Off Current		I _{CBO}	_		-0.5	μΑ	V _{CB} = -50V
Emitter Cut-Off Current	DCX122TH DCX142TH	I _{EBO}	_	_	-0.5 -0.5	μΑ	V _{EB} = -4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	_	_	-0.3	V	$I_C = -5mA$, $I_B = -0.25mA$
DC Current Transfer Ratio	DCX122TH DCX142TH	h _{FE}	100 100	250 250	600 600	_	I _C = -1mA, V _{CE} = -5V
Gain-Bandwidth Product*		f⊤	_	200	_	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

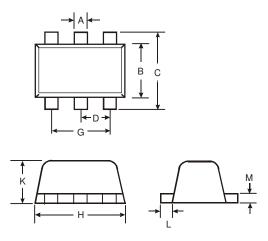
^{*} Transistor - For Reference Only





Package Outline Dimensions

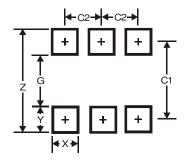
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT563								
Dim	Min	Max	Тур						
Α	0.15	0.30	0.20						
В	1.10	1.25	1.20						
С	1.55	1.70	1.60						
D	-	-	0.50						
G	0.90 1.10		1.00						
Н	1.50	1.70	1.60						
K	0.55	0.60	0.60						
L	0.10	0.30	0.20						
M 0.10 0.18 0.11									
All	Dimens	sions in	mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Υ	0.5
C1	1.7
C2	0.5



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